



# Bipolar NPN Bare Die – BTN6998

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## Part Description

The BTN6998 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6998.

## Key Parameters:

- VCBO = 60V
- VCEO = 50V
- VEBO = 5V
- hFE = 120-400 @ VCE = 6V, IC = 0.002A
- VCE(Sat) = 0.25V @ IC = 0.1A, IB = 10mA
- fT = 60 MHz @ VCE = 10V, IE = 0A
- COBO = 1pF @ VCB = 10V

## Features

Low VCE(sat). Designed to provide performance equivalent to TOSHIBA HN1B26FS

## Die Size (Unsawn)

260µm X 310µm, 10 Mils X 12 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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